

9. (New) A nitride semiconductor laser comprising
a GaN substrate having a single-crystal GaN layer at least on its
surface and

device-forming layers made of nitride semiconductor that are
formed on said GaN substrate,

wherein said single-crystal GaN layer is formed through a lateral-
growth process; and

said device-forming layer contacting said GaN substrate is made of
 $Al_aGa_{1-a}N (0 < a \leq 1)$.

10. (New) The nitride semiconductor laser according to claim 9, wherein
said device-forming layer contacting said GaN substrate is made of
 $Al_aGa_{1-a}N (0 < a < 0.3)$.

11. (New) The nitride semiconductor laser according to claim 9,
wherein said device-forming layer contacting said GaN substrate is made
of $Al_aGa_{1-a}N (0 < a < 0.1)$.

12. (New) The nitride semiconductor laser according to claim 9,
wherein said device-forming layer contacting said GaN substrate has a
thickness of not less than 1 μm .

13. (New) The nitride semiconductor laser according to claim 9,
wherein said device-forming layer contacting said GaN substrate has a
thickness of 3 to 10 μm .

14. (New) The nitride semiconductor laser according to claim 9,
wherein said device-forming layers include

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an $\text{Al}_a\text{Ga}_{1-a}\text{N}$ ($0 < a \leq 1$) layer contacting said GaN substrate, an n-type cladding layer containing Al, an active layer containing InGaN, and a p-type cladding layer containing Al.

15. (New) The nitride semiconductor laser according to claim 14, wherein said $\text{Al}_a\text{Ga}_{1-a}\text{N}$ layer contacting said GaN substrate has been grown without an impurity doping.

16. (New) The nitride semiconductor laser according to claim 14, wherein said device forming layers include a crack-preventing layer made of indium gallium nitride intervening between said $\text{Al}_a\text{Ga}_{1-a}\text{N}$ layer and said n-type cladding layer.